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APPLICATION N	Ю.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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INTERNATIONAL BUSINESS MACHINES CORPORATION				VU, HUNG K	
	DEPT. 18G BLDG. 300-482			ART UNIT	PAPER NUMBER
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Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)					
	10/026,146	VOLANT ET AL.					
Office Action Summary	Examiner	Art Unit					
	Hung Vu	2811					
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet w	ith the correspondence address					
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repleved in the provision of the period for reply specified above, the maximum statutory period for reply within the set or extended period for reply will, by statuted the period for reply will be period for reply		reply be timely filed ty (30) days will be considered timely. NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).					
Status							
1) Responsive to communication(s) filed on 24 I	November 2004.						
2a) This action is FINAL . 2b) ⊠ Thi	This action is FINAL. 2b)⊠ This action is non-final.						
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under	Ex parte Quayle, 1935 C.	D. 11, 453 O.G. 213.					
Disposition of Claims							
4) ⊠ Claim(s) 1-6 and 8-15 is/are pending in the ap 4a) Of the above claim(s) is/are withdra 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) 1-6 and 8-15 is/are rejected. 7) □ Claim(s) is/are objected to. 8) □ Claim(s) are subject to restriction and/	awn from consideration.						
Application Papers							
9) The specification is objected to by the Examin 10) The drawing(s) filed on is/are: a) acceptable and applicant may not request that any objection to the Replacement drawing sheet(s) including the correct of the oath or declaration is objected to by the Examin	cepted or b) objected to e drawing(s) be held in abeya ction is required if the drawing	nce. See 37 CFR 1.85(a). g(s) is objected to. See 37 CFR 1.121(d).					
Priority under 35 U.S.C. § 119		•					
 12) Acknowledgment is made of a claim for foreig a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document * See the attached detailed Office action for a list 	nts have been received. Its have been received in A prity documents have been au (PCT Rule 17.2(a)).	Application No received in this National Stage					
Attachment(s)							
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 Paper No(s)/Mail Date	Paper No	Summary (PTO-413) s)/Mail Date Informal Patent Application (PTO-152)					

U.S. Patent and Trademark Office PTOL-326 (Rev. 1-04)

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DETAILED ACTION

Request for Continued Examination

A request for continued examination (RCE) under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicants' submission filed on 11/24/04 has been entered. An action on the RCE follows.

Claim Rejections - 35 USC § 112

2. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claims 1-6 and 8-15 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

The specification does not disclose the resistance of the first conductor is approximately equal to the resistance of the second electrical conductor. Note that the specification only discloses the first and second conductors have equivalent sheet resistivities to solve the problem of resistance

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asymmetry. Sheet resistivities of the first and second conductors are equal does not necessarily

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mean the resistances of the first and second conductors are equal. In fact, there are other factors

can affect the resistance of the conductor, such as the length and the surface area of the

conductor.

3. Claims 1-6 and 8-15 are rejected under 35 U.S.C. 112, first paragraph, as failing to

comply with the enablement requirement. The claim(s) contains subject matter which was not

described in the specification in such a way as to enable one skilled in the art to which it pertains,

or with which it is most nearly connected, to make and/or use the invention.

The specification does not disclose the resistance of the first conductor is approximately equal to

the resistance of the second electrical conductor. Note that the specification only discloses the

first and second conductors have equivalent sheet resistivities to solve the problem of resistance

asymmetry. Sheet resistivities of the first and second conductors are equal does not necessarily

mean the resistances of the first and second conductors are equal. In fact, there are other factors

can affect the resistance of the conductor, such as the length and the surface area of the

conductor.

Claim Rejections - 35 USC § 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the

manner in which the invention was made.

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Claims 1, 4 and 5, insofar as in compliance with 35 USC, first paragraph, are rejected under 35 U.S.C. 103(a) as being unpatentable over Zhao et al. (PN 5,861,647, of record) in view of Lin (PN 6,303,423, of record).

Zhao et al. discloses, as shown in Figures 7 and 8, a passive electrical device comprising:

a first electrical conductor (20);

a second electrical conductor (52) disposed over the first electrical conductor;

a third electrical conductor (48) connecting the first electrical conductor to the second electrical conductor, wherein the first, second and third electrical conductors are disposed on a semiconductor substrate (28,30) and wherein the sheet resistivity of the first electrical conductor is approximately equal to the sheet resistivity of the second electrical conductor. Note that the first and the second electrical conductors comprise the same material, it is inherent that the sheet resistivity of the first electrical conductor is approximately equal to that of the second electrical conductor [see Col. 3, lines 2-6 and 56-57];

wherein the third electrical conductor consists essentially of one substantially uniform chemical composition (tungsten, aluminum or copper) [see Col. 3, lines 40-41].

Zhao et al. discloses the third electrical conductor has a thickness which separates the first electrical conductor from the second electrical conductor by a distance in a range of 2.3 microns [see Col. 3, lines 23-27, note that the third electrical conductor 48 is formed in the dielectric layer 36 which is the combination of layers 38, 40 and 42]. Zhao et al. does not disclose the third electrical conductor has the thickness which separates the first electrical conductor from the second electrical conductor by a distance in a range of approximately three microns to approximately four microns. However, Lin discloses a device having a third electrical conductor

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(38) that has a thickness which separates a first electrical conductor (16) from a second electrical conductor (40) by a distance in a range of approximately three microns to approximately four microns. Note Figures 1, 2, 4, and Col. 8, line 52 – Col. 9, line 29, note that the third electrical conductor 38 is formed in the dielectric layers 18 and 20 having the thickness as claimed]. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the third electrical conductor of Zhao et al. having a thickness, as taught by Lin in order to have a desired inductance according to electrical design requirements.

With regard to claim 4, Zhao et al. and Lin disclose the first, second and third electrical conductors consist essentially of copper [see Col. 3, lines 2-6, 39-43 and 56-57].

With regard to claim 5, Zhao et al. and Lin disclose the first and third electrical conductors consist essentially of copper, and the second electrical conductor consists essentially of aluminum [see Col. 3, lines 2-6, 39-43 and 56-57].

5. Claims 1-4, 6 and 9, insofar as in compliance with 35 USC, first paragraph, are rejected under 35 U.S.C. 103(a) as being unpatentable over Wen et al. (PN 6,083,802, of record) in view of Lin (PN 6,303,423, of record).

Wen et al. discloses, as shown in Figures 12 and 13, a passive electrical device comprising:

- a first electrical conductor (20);
- a second electrical conductor (28) disposed over the first electrical conductor;

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a third electrical conductor (26) connecting the first electrical conductor to the second electrical conductor, wherein the first, second and third electrical conductors are disposed on a semiconductor substrate (14) and wherein the sheet resistivity and the resistance of the first electrical conductor is approximately equal to the sheet resistivity and the resistance of the second electrical conductor. Note that the first and the second electrical conductors comprise the same material (copper), it is inherent that the sheet resistivity of the first electrical conductor is approximately equal to that of the second electrical conductor [see Col. 3, lines 5-14 and 53-65]. Also note that Wen et al. discloses the second conductor (28) is formed by repeating the same process for forming the first conductor (20), it is inherent that the resistance of the first conductor is approximately equal to that of the second conductor [see Col. 3, lines 12 – 14 and lines 57 – 64],

wherein the third electrical conductor consists essentially of one substantially uniform chemical composition (tungsten, aluminum or copper) [see Col. 3, lines 55-57].

Wen et al. discloses the third electrical conductor has a thickness which separates the first electrical conductor from the second electrical conductor by a distance in a range of approximately 5 to 10 microns [see Col. 3, lines 39-41, note that the third electrical conductor 26 is formed in the dielectric layer 24]. Wen et al. does not disclose the third electrical conductor has the thickness which separates the first electrical conductor from the second electrical conductor by a distance in a range of approximately three microns to approximately four microns. However, Lin discloses a device having a third electrical conductor (38) that has a thickness which separates a first electrical conductor (16) from a second electrical conductor (40) by a distance in a range of approximately three microns to approximately four microns. Note

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Figures 1, 2, 4, and Col. 8, line 52 – Col. 9, line 29, note that the third electrical conductor 38 is formed in the dielectric layers 18 and 20 having the thickness as claimed]. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the third electrical conductor of Wen et al. having a thickness, as taught by Lin in order to have a desired inductance according to electrical design requirements.

With regard to claim 2, Wen et al. and Lin disclose each of the first, second and third electrical conductors has a respective thickness, and the thickness of the first electrical conductor is approximately equal to the thickness of the second electrical conductor [see Col. 3, lines 5-14 and 53-65].

With regard to claim 3, Wen et al. and Lin disclose each of the first, second and third electrical conductors has a respective thickness, and the thickness of the first conductor is approximately equal to the thickness of the second electrical conductor and being approximately one-half the thickness of the third electrical conductor.

With regard to claim 4, Wen et al. and Lin disclose the first, second and third electrical conductors consist essentially of copper [see Col. 3, lines 5-14 and 53-65].

With regard to claim 6, Wen et al. and Lin disclose each of the first and second electrical conductors has a respective thickness in a range of approximately five to 20 microns (within the range of approximately two to approximately 32 microns) [see Col. 3, lines 5-14 and 53-65].

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With regard to claim 9, Wen et al., as shown in Figure 3 and 13, the inductor device comprising: a semiconductor substrate (14);

first, second and third electrical conductors (24,26,28) provided on the substrate, wherein the first and second electrical conductors each has a resistance which is approximately equal. Note that Wen et al. discloses the second conductor (28) is formed by repeating the same process for forming the first conductor (20), it is inherent that the resistance of the first conductor is approximately equal to that of the second conductor [see Col. 3, lines 12 - 14 and lines 57 - 64]

wherein the third electrical conductor consists essentially of one substantially uniform chemical composition (tungsten, aluminum or copper) [see Col. 3, lines 55-57].

Wen et al. discloses the third electrical conductor has a thickness in a range of approximately 5 to 10 microns [see Col. 3, lines 39-41, note that the third electrical conductor 26 is formed in the dielectric layer 24]. Wen et al. does not disclose the third electrical conductor has the thickness which separates the first electrical conductor from the second electrical conductor by a distance in a range of approximately three microns to approximately four microns and the semiconductor substrate comprises silicon. However, Lin discloses a device having a third electrical conductor (38) that has a thickness which separates a first electrical conductor (16) from a second electrical conductor (40) by a distance in a range of approximately three microns to approximately four microns and a semiconductor substrate (10) comprises silicon. Note Figures 1, 2, 4, and Col. 7, lines 28 – 29 and Col. 8, line 52 – Col. 9, line 29, note that the third electrical conductor 38 is formed in the dielectric layers 18 and 20 having the thickness as claimed. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form

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the third electrical conductor of Wen et al. having a thickness, as taught by Lin in order to have a desired inductance according to electrical design requirements, and to form the semiconductor substrate of Wen et al. comprising silicon because silicon is one of the materials that is commonly used to form the substrate.

6. Claims 5 and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wen et al. (PN 6,083,802, of record) in view of Lin (PN 6,303,423, of record) and further in view of Zhao et al. (PN 5,861,647, of record).

With regard to claim 5, Wen et al. and Lin taught the invention substantially as claimed, including the passive electrical device as cited in the rejection of claim above. Wen et al. and Lin also taught the first, second and third electrical conductors consist essentially of copper. Wen et al. and Lin did not specifically teach the second electrical conductor consists essentially of aluminum. However, Zhao et al. taught a second electrically conductor (52) consists essentially of aluminum or copper [see Figures 8-9, Col. 3, lines 56-57]. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the second electrical conductor of Wen et al. and Lin consists essentially of aluminum, such as taught by Zhao et al. because aluminum and copper are commonly used to form the conductor for they have lower resistance, and they are interchangeable.

With regard to claim 8, Wen et al., Lin and Zhao et al. disclose the second electrical conductor has a substantially uniform thickness in a range of approximately five to 20 microns (within the range of approximately four to approximately six microns) [see Col. 3, lines 5-14 and 53-65].

7. Claims 10-11 and 13-15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wen et al. (PN 6,083,802, of record) in view of Lin (PN 6,303,423, of record) and further in view of Johnson et al. (PN 6,534,374, of record).

Wen et al. and Lin taught the invention substantially as claimed, including the passive electrical device as cited in the rejection of claim above. Wen et al. and Lin also taught the semiconductor substrate comprises silicon. Wen et al. and Lin did not teach the semiconductor substrate comprises silicon and germanium. However, Johnson et al. taught a semiconductor substrate (20) comprises silicon and germanium [see Figures 10 and 16 and Col. 5, lines 2-6]. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the semiconductor substrate of Wen et al. and Lin comprising silicon and germanium such as taught by Johnson et al. since silicon and germanium are the materials that are commonly used to form the substrate.

With regard to claim 11, Wen et al., Lin and Johnson et al. taught the substrate comprises silicon on insulator substrate [see Col. 5, lines 2-6].

With regard to claim 13, Wen et al., Lin and Johnson et al. taught the second electrical conductor is disposed over the first electric conductor [see Figures 8 and 13].

With regard to claim 14, Wen et al., Lin and Johnson et al. taught the first and second electrical conductors are spiral shaped [see Figure 2].

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With regard to claim 15, Wen et al., Lin and Johnson et al. taught each of the first and the second electrical conductors has a sheet resistivity, the sheet resistivity of the first electrical conductor being approximately equal to the sheet resistivity of the second electrical conductor. Note that the first and the second conductors comprise the same material (copper), it is inherent that the sheet resistivity of the first conductor is approximately equal to that of the second conductor [see Col. 3, lines 5-14 and 53-65].

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8. Claims 12, 13 and 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wen et al. (PN 6,083,802, of record) in view of Lin (PN 6,303,423, of record) and further in view of Ito (PN 4,758,896, of record).

Wen et al. and Lin taught the invention substantially as claimed, including the passive electrical device as cited in the rejection of claim above. Wen et al. and Lin also taught the semiconductor substrate comprises silicon. Wen et al. and Lin did not teach the semiconductor substrate comprises silicon and germanium. However, Ito taught a semiconductor substrate (10) comprises silicon-on-sapphire [see Figures 1 and 3 and Col. 8, lines 9-36]. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the semiconductor substrate of Wen et al. and Lin comprising silicon and germanium such as taught by Ito since silicon-on-sapphire are the materials that are commonly used to form the substrate.

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With regard to claim 13, Wen et al., Lin and Ito taught the second electrical conductor is disposed over the first electric conductor [see Figures 8 and 13].

With regard to claim 15, Wen et al., Lin and Ito taught each of the first and the second electrical conductors has a sheet resistivity, the sheet resistivity of the first electrical conductor being approximately equal to the sheet resistivity of the second electrical conductor. Note that the first and the second conductors comprise the same material (copper), it is inherent that the sheet resistivity of the first conductor is approximately equal to that of the second conductor [see Col. 3, lines 5-14 and 53-65].

Response to Arguments

9. Applicant's arguments filed 11/24/04 have been fully considered but they are not persuasive.

It is argued, at pages of the Remarks, that Zhao et al. does not disclose a first conductor having a "resistance" approximately equal to a "resistance" of a second conductor. This argument is not convincing due to the above rejection under 35 USC 112, first paragraph.

It is argued, at pages of the Remarks, that Wen et al. does not disclose a first conductor having a "resistance" approximately equal to a "resistance" of a second conductor. This argument is not convincing because Wen et al. discloses the second conductor (28) is formed by repeating the same process for forming the first conductor (20), it is inherent that the resistance of the first conductor is approximately equal to that of the second conductor [see Col. 3, lines 12 - 14 and

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lines 57 - 64].

Conclusion

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10. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Hung K. Vu whose telephone number is (571) 272-1666. The

examiner can normally be reached on Mon-Thurs 6:00-3:30, alternate Friday 7:00-3:30, Eastern

Time.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Eddie C. Lee can be reached on (571) 272-1732. The Central Fax Number for the

organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-0956.

Vu

January 17, 2005

Hung Vu

Primary Examiner